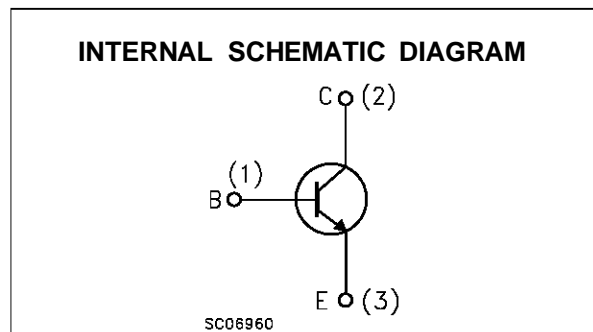
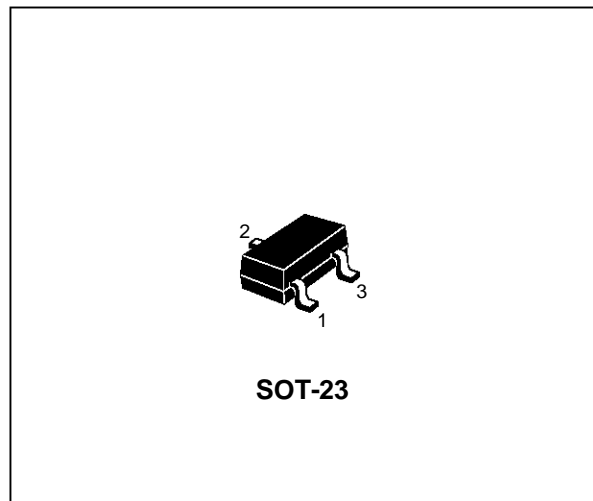


SMALL SIGNAL NPN TRANSISTOR

Type	Marking
SOA06	1GT

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- MEDIUM CURRENT AF AMPLIFICATION
- PNP COMPLEMENTS IS SOA56



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	80	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	80	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	4	V
I_C	Collector Current	0.5	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	350	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

SOA06

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	350	°C/W
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• Mounted on a ceramic substrate area = 15 x 15 x 0.5 mm

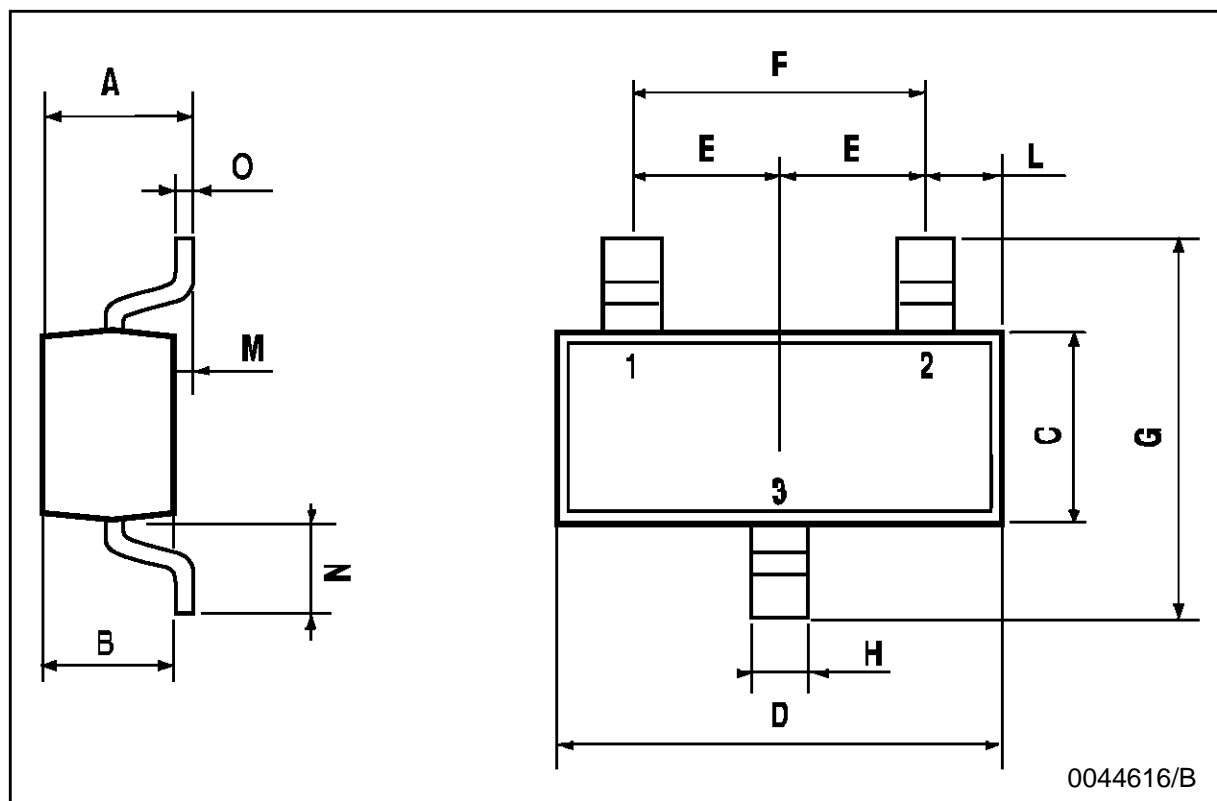
ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 80\text{ V}$			100	nA
I_{CEO}	Collector Cut-off Current ($I_E = 0$)	$V_{CE} = 60\text{ V}$			100	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 1\text{ mA}$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100\text{ }\mu\text{A}$	4			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 100\text{ mA}$ $I_B = 10\text{ mA}$			0.25	V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = 100\text{ mA}$ $V_{CE} = 1\text{ V}$			1.2	V
h_{FE}^*	DC Current Gain	$I_C = 10\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 100\text{ mA}$ $V_{CE} = 1\text{ V}$	50 50			
f_T	Transition Frequency	$I_C = 10\text{ mA}$ $V_{CE} = 2\text{ V}$ $f = 100\text{ MHz}$	100			MHz

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



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